



# 11th International "Hiroshima" Symposium on the Development and Application of Semiconductor Tracking Detectors (HSTD11) in conjunction with 2nd Workshop on SOI Pixel Detectors (SOIPIX2017) at OIST, Okinawa, Japan

## Thursday, 14 December 2017

### Session14 - Conference Center (16:10 - 17:50)

-Conveners: Manabu Togawa

time	[id] title	presenter
16:10	[164] Development of a monolithic pixel sensor based on SOI technology for the ILC vertex detector	ONO, Shun
16:30	[147] Beam test results of a monolithic pixel detector designed in SOI 200nm technology.	BUGIEL, Szymon
16:50	[16] Radiation hardness of silicon-on-insulator pixel device	HARA, Kazuhiko
17:10	[45] Investigation of Radiation Hardness Improvement by Applying Back-gate Bias for FD-SOI MOSFETs	Prof. KURACHI, Ikuo
17:30	[48] Total ionizing dose effects on the SOI pixel sensor for X-ray astronomical use	MORI, Koji